

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

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1-8. (Canceled).

9. (New) A ceramic heater used in an industrial field of semiconductors, comprising:

a disk-shaped ceramic substrate; and

a heat-generation pattern disposed on a surface of said disk-shaped ceramic substrate,

wherein said disk-shaped ceramic substrate has a diameter of 200 mm or more and said disk-shaped ceramic substrate is made of at least one selected from a group essentially consisting of nitride ceramics and carbide ceramics; and

said heat-generation pattern has a bending portion which describes an arc having a curvature radius within a range of 0.1 mm to 20 mm; and

a semiconductor wafer is heated on a surface opposite to the surface of the ceramic substrate forming the heat-generating body.

10. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein through-holes for inserting support pins are formed on the ceramic substrate.

11. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein the bending pattern is arranged along outer regions of said disk-shaped ceramic substrate.

12. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein a pattern width in the bending portion of the heat-generation pattern is generally constant.

13. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein the ceramic heater is used within a temperature range from 150 to 800°C.

14. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein the ceramic substrate has a diameter more than or equal to 300 mm.

15. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 9, wherein the ceramic substrate is made of aluminum nitride or silicon carbide.

16. (New) A ceramic heater used in an industrial field of semiconductors, comprising:

a disk-shaped ceramic substrate; and

a heat-generation pattern disposed within said disk-shaped ceramic substrate,

wherein said disk-shaped ceramic substrate has a diameter of 200 mm or more

and said disk-shaped ceramic substrate is made of at least one selected from a group essentially consisting of nitride ceramics and carbide ceramics; and

said heat-generation pattern has a bending portion which describes an arc having a curvature radius within a range of 0.1 mm to 20 mm.

17. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein through-holes for inserting support pins are formed on the ceramic substrate.

18. (New) The ceramic heater used in as industrial field of semiconductors, according to claim 16, wherein the bending pattern is arranged along outer regions of the disk-shaped ceramic substrate.

19. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein a pattern width in the bending portion of the heat-generation pattern is generally constant.

20. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein the ceramic heater is used within a temperature range from 150 to 800°C.

21. (New) The ceramic heater used in an industrial field of semiconductors, according to claim 16, wherein the ceramic substrate has a diameter more than or equal to 300 mm.

22. (New) The ceramic heater used in as industrial field of semiconductors, according to claim 16, wherein the ceramic substrate is made of aluminum nitride or silicon carbide.